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Kind regards,

Team Nexperia



# PMBTA42 300 V, 100 mA NPN high-voltage transistor Rev. 05 – 12 December 2008

**Product data sheet** 

# 1. Product profile

#### 1.1 General description

NPN high-voltage transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PMBTA92.

#### **1.2 Features**

High voltage (max. 300 V)

#### 1.3 Applications

Telephony and professional communication equipment

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	300	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		$I_{\rm C} = 1  \rm{mA}$	25	-	-	
		I <sub>C</sub> = 10 mA	40	-	-	
		I <sub>C</sub> = 30 mA	40	-	-	

### 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		3
3	collector		



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### 3. Ordering information

Type number <sup>[1]</sup>	Package		
	Name	Description	Version
PMBTA42	-	plastic surface-mounted package; 3 leads	SOT23
PMBTA42/DG			

### 4. Marking

Type number <sup>[1]</sup>	Marking code <sup>[2]</sup>	
PMBTA42	*1D	
PMBTA42/DG	*BV	

- [2] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

# 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	300	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	300	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

#### 300 V, 100 mA NPN high-voltage transistor

# 6. Thermal characteristics

Table 7.

Characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

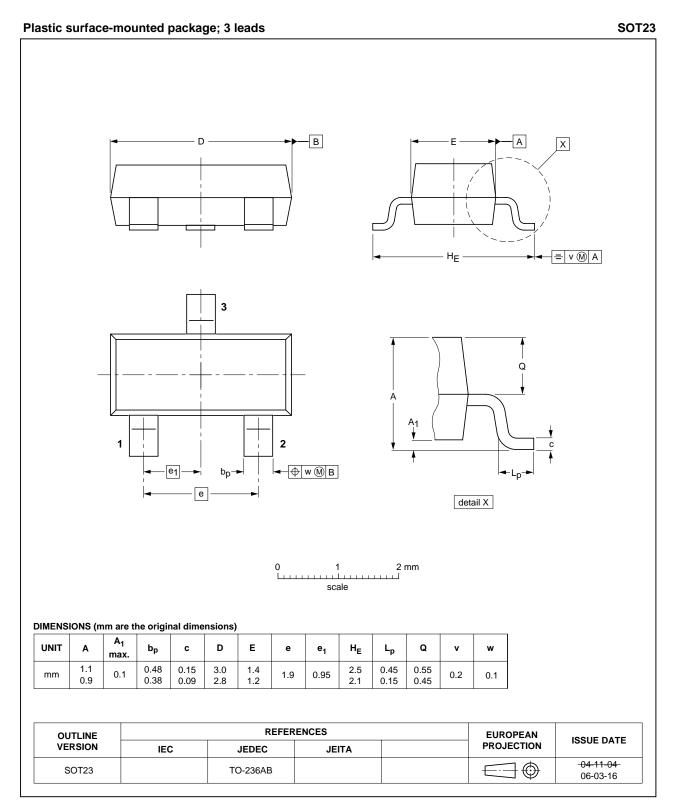
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

# 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 200 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 6 V; I_C = 0 A$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V				
		$I_{\rm C} = 1  \rm{mA}$	25	-	-	
		I <sub>C</sub> = 10 mA	40	-	-	
		I <sub>C</sub> = 30 mA	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C}$ = 20 mA; $I_{\rm B}$ = 2 mA	-	-	500	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{\rm C}$ = 20 mA; $I_{\rm B}$ = 2 mA	-	-	900	mV
C <sub>re</sub>	feedback capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 20 \ V; \ I_{C} = i_{c} = 0 \ A; \\ f = 1 \ MHz \end{array}$	-	-	3	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 20 V; I <sub>C</sub> = 10 mA; f = 100 MHz	50	-	-	MHz

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### 8. Package outline



#### Fig 1. Package outline SOT23 (TO-236AB)

#### 300 V, 100 mA NPN high-voltage transistor

### 9. Packing information

#### Table 8. Packing methods

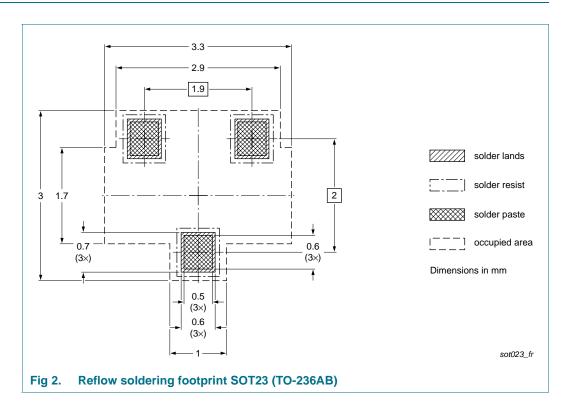
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Package Description		Packing quantity		
				3000	10000	
PMBTA42	SOT23	4 mm pitch, 8 mm tape and reel		-215	-235	
PMBTA42/DG						

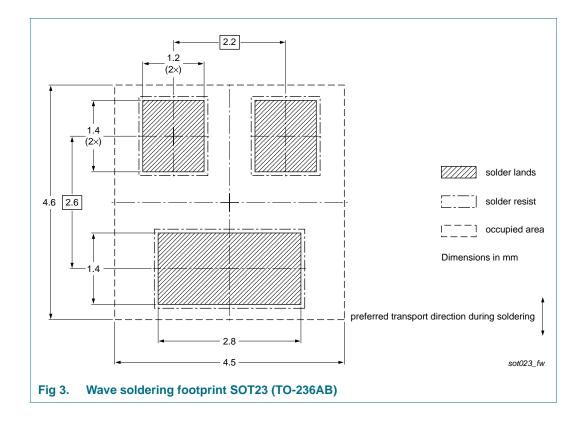
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

[2] /DG: halogen-free

# 10. Soldering



#### 300 V, 100 mA NPN high-voltage transistor



#### 300 V, 100 mA NPN high-voltage transistor

# 11. Revision history

Table 9. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA42_5	20081212	Product data sheet	-	PMBTA42_4
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the n	ew company name whe	ere appropriate.
	<ul> <li>Type numb</li> </ul>	er PMBTA42/DG added		
	Table 4 "Ma	urking codes": enhanced		
	Section 12	"Legal information": updated	t	
PMBTA42_4	20040122	Product specification	-	PMBTA42_3
PMBTA42 3	19990422	Product specification	-	PMBTA42 43 CNV 2

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### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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#### 300 V, 100 mA NPN high-voltage transistor

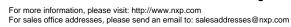
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